



Silicon Wafer Japan TC Chapter

Japan Standards Winter 2021 Meetings

Friday, January 15, 2021

SEMI Japan office, Tokyo, Japan

<10:00–16:00 JST>

AGENDA(Draft)

	Time
1 Welcome/Call to Order	10:00
1.1 Introductions	
1.2 Required Elements (Membership Requirements, Antitrust and Intellectual Property Reminders, and Effective Meeting Guidelines)	
1.3 Agenda Review	
2 Review of Previous Meeting Minutes	00:00
3 Ballot Review	00:00
3.1 Cycle 3-2020 submitted by the NA TC Chapter (the GCS authorized to transfer responsibilities for Letter Ballot review from the NA TC Chapter to the Japan Chapter of Silicon Wafer Committee for these documents)	
3.1.1 Doc. 6363, Revision of SEMI M52-0214 With Title Change To: Guide For Specifying Scanning Surface Inspection Systems For Silicon Wafers For The 130 nm To 5 nm Technology Generations	
3.1.2 Doc. 6613, Reapproval of SEMI M20-0215, Practice for Establishing a Wafer Coordinate System	
3.2 Cycle 8-2020 submitted by the Japan TC Chapter	
3.2.1 Doc. 6680 - Reapproval of SEMI M77-1015, Test Method for Determining Wafer Near-Edge Geometry Using Roll-Off Amount, ROAcations	
3.2.2 Doc. 6681 - Reapproval of SEMI MF1451-0707 (Reapproved 0319), Test Method for Measuring SORI on Silicon Wafers by Automated Noncontact Scanning	
3.3 Cycle 2-2020 submitted by the NA TC Chapter (the GCS authorized to transfer responsibilities for Letter Ballot review from the NA TC Chapter to the Japan Chapter of Silicon Wafer Committee for these documents)	
3.3.1 Doc. 5981, New Standard: Test Method For Recombination Lifetime Of The Epilayer Of The Silicon Epitaxial Wafer (p/p+, n/n+) By The Short Wavelength Excitation Microwave Photoconductive Decay Method	
3.3.2 Doc. 6526B, New Standard: Test Method for Bulk Micro Defect Density and Denuded Zone Width in Annealed Silicon Wafers by Optical Microscopy after Preferential Etching	
4 Subcommittee & Task Force Reports	00:00
4.1 International Advanced Wafer Geometry TF	
4.2 Japan Test Method TF	

- 4.3 International Advanced Surface Inspection TF
- 4.4 International 450 mm Shipping Box TF
- 4.5 International Polished Wafers TF
- 4.6 International Epitaxial Wafers TF
- 4.7 International Annealed Wafers TF
- 4.8 International SOI Wafers TF
- 4.9 International Terminology TF

5 Liaison Report

- 5.1 Europe TC Chapter
- 5.2 North America TC Chapter
- 5.3 GCS Report

6 Staff Report

7 Old Business

00:00

- 7.1 Project Period Review
 - 7.1.1 #5772 SNARF for: Revision of MF391-0310: Test Methods for Minority Carrier Diffusion Length in Extrinsic Semiconductors by Measurement of Steady-state Surface photovoltage
 - 7.1.2 #5981 SNARF for: NEW STANDARD: TEST METHOD FOR RECOMBINATION LIFETIME OF THE EPILAYER OF THE SILICON EPITAXIAL WAFER (p/p+, n/n+) BY THE SHORT WAVELENGTH EXCITATION MICROWAVE PHOTOCONDUCTIVE DECAY METHOD
- 7.2 5 Year Review Check
 - 7.2.1 M51-1012: Test Method for Characterizing Silicon Wafer by Gate Oxide Integrity
 - 7.2.2 M60-1014: Test Method for Time Dependent Dielectric Breakdown Characteristics of SiO₂ Films for Si Wafer Evaluation

8 New Business

00:00

- 8.1 Committee Leadership Change

9 Action Item Review

00:00

- 9.1 Open Action Items
- 9.2 New Action Items

10 Next Meeting and Adjournment

16:00

- 10.1 The next meeting is scheduled for <date> at <event/location>.